

MEDIUM POWER NPN SILICON TRANSISTOR

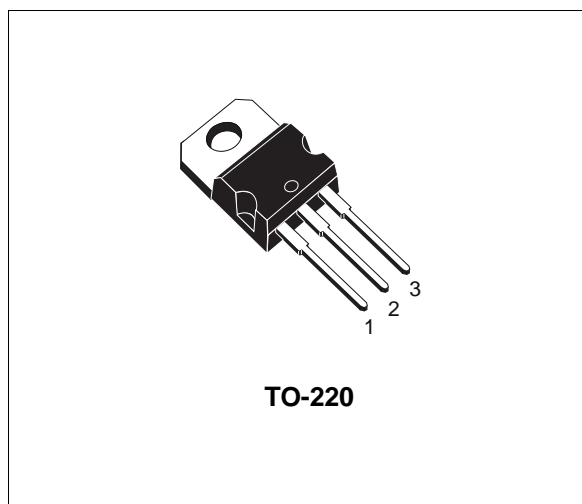
- SGS-THOMSON PREFERRED SALESTYPE
- NPN TRANSISTOR
- FAST SWITCHING SPEED
- LOW COLLECTOR-EMITTER SATURATION

APPLICATIONS

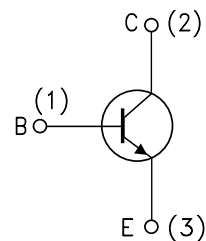
- SWITCHING REGULATORS
- MOTOR CONTROL

DESCRIPTION

The BUV26 is a Multiepitaxial Planar NPN Transistor in TO-220 package. It is intended for use in high frequency and efficiency converters, switching regulators and motor control.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	180	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	90	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Emitter Current	14	A
I_{CM}	Collector Peak Current ($t_p < 10ms$)	25	A
I_B	Base Current	4	A
I_{BM}	Base Peak Current ($t_p < 10ms$)	6	A
P_{tot}	Total Dissipation at $T_c < 25^\circ C$	85	W
P_{tot}	Total Dissipation at $T_c < 60^\circ C$	65	W
T_{stg}	Storage Temperature	-65 to +175	$^\circ C$
T_j	Max. Operating Junction Temperature	175	$^\circ C$

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.76	°C/W
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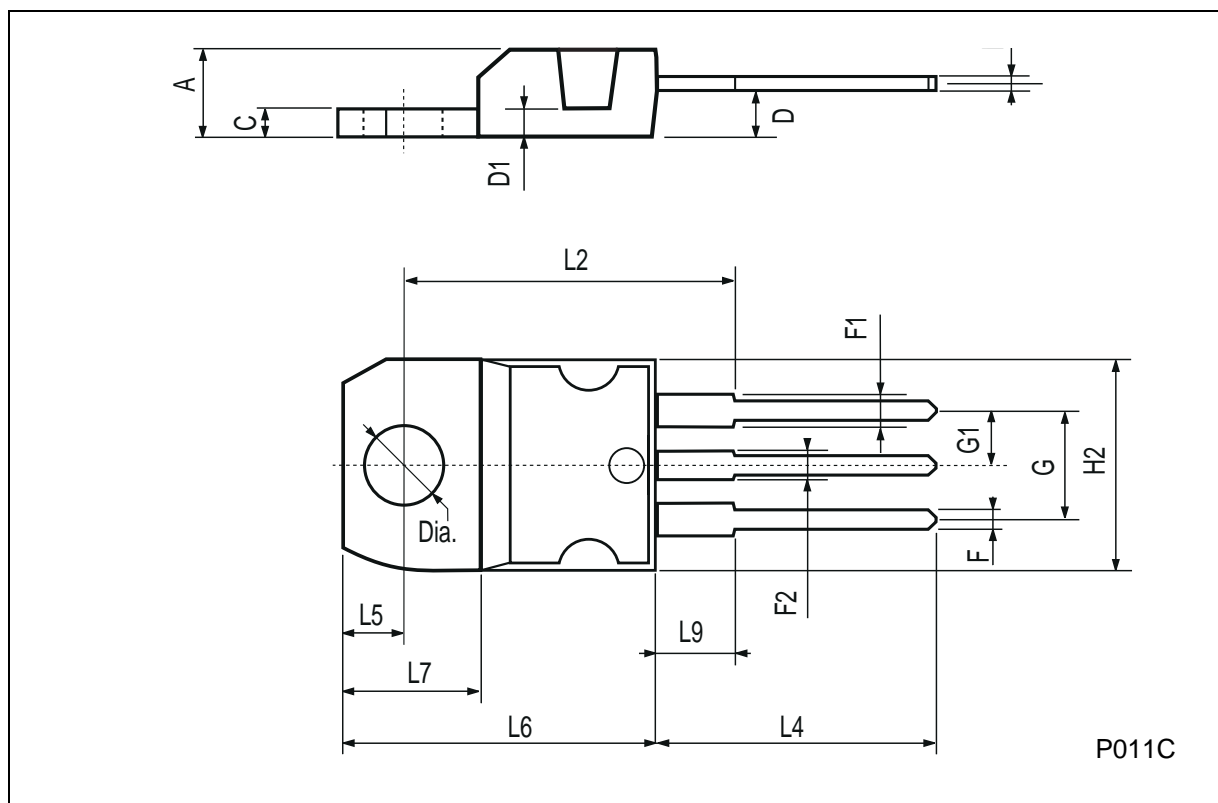
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEr}	Collector Cut-off Current (R _{BE} = 50Ω)	V _{CE} = 180V T _c = 125°C			3	mA
I _{CEX}	Collector Cut-off Current	V _{CE} = 180V V _{BE} = -1.5V T _c = 125°C			1	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 0.2 A L = 25mH	90			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 50mA	7		30	V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 6A I _B = 0.6A I _C = 12A I _B = 1.2A			0.6 1.5	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = 12A I _B = 1.2A			2	V
t _{on} t _s t _f	RESISTIVE LOAD Turn-on Time Storage Time Fall Time	V _{CC} = 50V I _C = 12A V _{BE} = - 6V I _{B1} = 1.2A R _{BB} = 2.5Ω		0.4 0.45 0.12	0.6 1 0.25	ms μs μs
t _s t _f	INDUCTIVE LOAD Storage time Fall Time	V _{CC} = 50V I _C = 12A V _{BE} = - 5V I _{B1} = 1.2A L _B = - 0.5μH		0.5 0.04		μs μs
t _s t _f	Storage Time Fall Time	V _{CC} = 50V I _C = 12 A V _{BE} = - 5V I _{B1} = 1.2A L _B = - 0.5μH T _j = 125°C			2 0.15	μs μs

* Pulsed: Pulse duration = 300μs, duty cycle = 1.5 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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